Patent Application Docket No. 45688-00002USPT

## In the Claims

1	1. (Currently An ended) A flip-chip light-emitting device, comprising.
2	a transparent substrate comprising a main surface and a surface opposite to said
3	main surface, wherein said surface opposite to said main surface is the light-emitting surface of
4	said device,
5	a semiconductor stacked structure arranged over-a said main surface of said
6	transparent substrate wherein said stacked structure comprises an n-type GaN-based III-V Group
7	compound semiconductor layer adjacent to said main surface and a p-type GaN-based III-V
8	Group compound semice nductor layer adjacent to said n-type semiconductor layer;
9	a first electrode being in electrical contact with said n-type se niconductor layer,
10	and
11	a second electrode being in electrical contact with said p-type semiconductor
12	layer;
13	wherein said second electrode has good reflectivity of light and, covers most of
14	the outer surface of said p-type semiconductor layer and is positioned opposite to said light-
15	emitting surface of said substrate.
1	2 (Original) The device of Claim 1 wherein said stacked structure fi rther comprises an
2	active layer placed between said n-type semiconductor layer and said p-t/pe semiconductor
3	layer.

3 (Original) The device of Claims 1 or 2 further comprising an insulating layer at least coated on the side surface of the stacked structure, a portion of said first electrode and a portion of said second electrode.

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- 4 (Original) The device of Claims 1 or 2 further comprising a base which has a first and a second conductive portions respectively connected to said first and second electrodes.
- 1 5. (Original) The device of Claim 4 wherein said base can be a conductive lead frame, a glass lead frame, a circuit board or a thin-film circuit.
- 6. (Original) The device of Claims 1 or 2 wherein said second electrode is a multi-layer structure comprising a light-transmitting conductive layer and a layer of aluminum (AL) or silver (Ag).
- 7. (Original) The device of Claims 1 or 2 wherein said second electrode is a multi-layer structure of nickel/go d/titanium/ aluminum (Ni/Au/Ti/Al), Indium-Tir Oxide/aluminum (ITO/Al) or Indium-Tin Oxide/silver (ITO/Ag).
  - 8. (Currently Ar lended) A flip-chip light-emitting device, comprising
  - a transpa ent substrate comprising a main surface and a surface opposite to said main surface, wherein said surface opposite to said main surface is the light-emitting surface of said device;
- a semico iductor stacked structure arranged over [a] said main surface of said transparent substrate wherein said stacked structure comprises an p-type GaN-based III-V group compound semiconduct in layer adjacent to said main surface and a n-type GaN-based III-V
- 8 Group compound semice inductor layer adjacent to said p-type semiconductor layer,

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9	a first electrode being in electrical contact with said n-type semiconductor layer
10	and
11	a second electrode being in electrical contact with said p-type semiconductor
12	layer,
13	wherein aid first electrode has good reflectivity of light-and, and covers most of
14	the outer surface of said n-type semiconductor layer and is positioned opposite to said light-
15	emitting surface of said substrate.
1	9. (Original) Tue device of Claim 8 wherein said stacked structure further comprises an
2	active layer placed betw en said n-type semiconductor layer said the p-type semiconductor layer.
l	10. (Original) The device of Claims 8 or 9 further comprising an insulating layer at least
2	coated on the side surface of the stacked structure, a portion of said first electrode and a portion
3	of said second electrode
,	11 (Original) The device of Chains 0 as 0.5 d
1	11. (Original) The device of Claims 8 or 9 further comprising a base which has a first
2	and a second conductive portions respectively connected to said first and second electrodes.
1	12. (Original) The device of Claim 11 wherein said base can be a conductive lead frame,
2	a glass lead trame, a circ sit board or a thin-film circuit.
1	13. (Original) The device of Claims 8 or 9 wherein said second electrode is a multi-layer
2	structure comprising a light-transmitting conductive layer and a layer of aluminum (Al) or silver
3	(Ag)

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- 14. (Original) The device of Claims 8 or 9 wherein said second electrode is a multi-layer · 1 2
  - structure of titanium/al ıminum (Ti/Al), titanium/silver (Ti/Ag), Indium-Tin Oxide/aluminum
  - (ITO/Al) or Indium-Tin Oxide/silver (ITO/Ag).